



A Product Line of
Diodes Incorporated



ZXTP03200BG 200V PNP Low $V_{CE(sat)}$ transistor in SOT223

Summary

$BV_{CEO} > -200V$

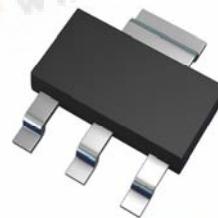
$BV_{ECO} > -2V$

$I_{C(\text{cont})} = 2A$

$V_{CE(sat)} < -160mV @ -1A$

$R_{CE(sat)} = 135m\Omega$

$P_D = 3W$



Description

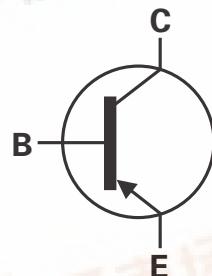
Packaged in the SOT223 outline this new 5th generation low saturation 200V PNP transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions

Features

- 2 Amps continuous current
- Up to 5 Amps peak current
- Very low saturation voltage
- Enhanced switching performance

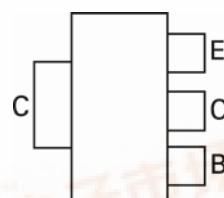
Applications

- DC-DC conversion



Ordering Information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP03200BGTA	7	12	1000



Pin out - top view

Device Marking

ZXTP03200BG

ZXTP03200BG

Absolute Maximum Ratings

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V_{CBO}	-220	V
Collector-Emitter Voltage	V_{CEO}	-200	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current ^(a)	I_C	-2	A
Base Current	I_B	-1	A
Peak Pulse Current	I_{CM}	-5	A
Power Dissipation at $T_A=25^\circ\text{C}$ ^(a) Linear Derating Factor	P_D	1.25 10	W mW/ $^\circ\text{C}$
Power Dissipation at $T_A=25^\circ\text{C}$ ^(b) Linear Derating Factor	P_D	1.65 13.2	W mW/ $^\circ\text{C}$
Power Dissipation at $T_A=25^\circ\text{C}$ ^(c) Linear Derating Factor	P_D	3 24	W mW/ $^\circ\text{C}$
Power Dissipation at $T_A=25^\circ\text{C}$ ^(d) Linear Derating Factor	P_D	5.8 46.5	W mW/ $^\circ\text{C}$
Power Dissipation at $T_C=25^\circ\text{C}$ ^(e) Linear Derating Factor	P_D	11.9 95.2	W mW/ $^\circ\text{C}$
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to 150	$^\circ\text{C}$

Thermal Resistance

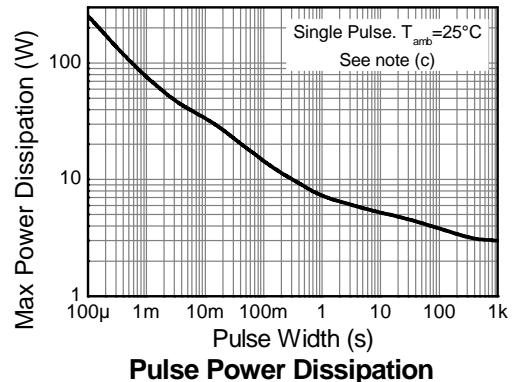
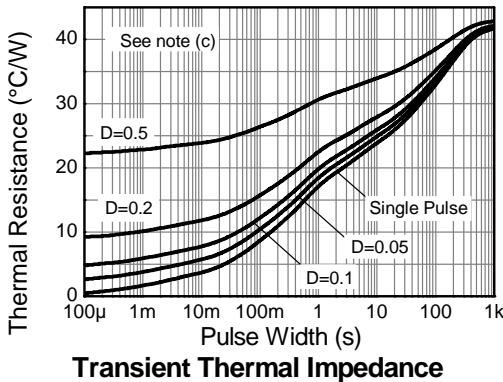
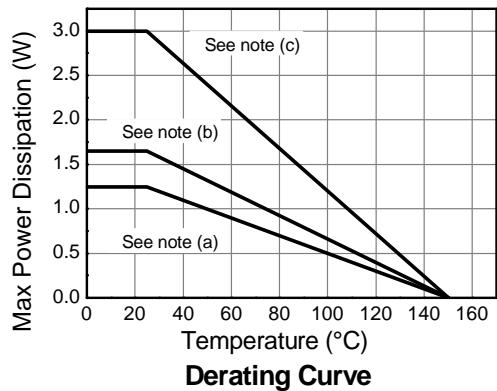
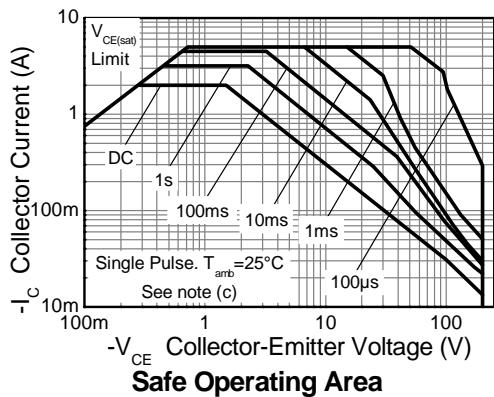
Parameter	Symbol	Value	Unit
Junction to Ambient ^(a)	$R_{\theta JA}$	100	$^\circ\text{C/W}$
Junction to Ambient ^(b)	$R_{\theta JA}$	76	$^\circ\text{C/W}$
Junction to Ambient ^(c)	$R_{\theta JA}$	41.6	$^\circ\text{C/W}$
Junction to Ambient ^(d)	$R_{\theta JA}$	21.5	$^\circ\text{C/W}$
Junction to Lead ^(e)	$R_{\theta JL}$	10.5	$^\circ\text{C/W}$

NOTES:

- (a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.
- (d) As (c) above measured at $t < 5$ seconds.
- (e) Junction to Lead from Collector Tab.Typical

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Thermal Characteristics



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Electrical Characteristics (at $T_{amb} = 25^\circ C$ unless otherwise stated)

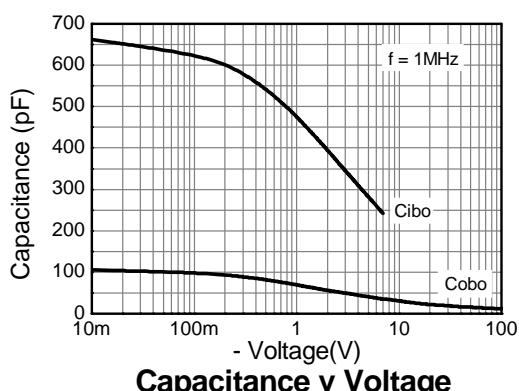
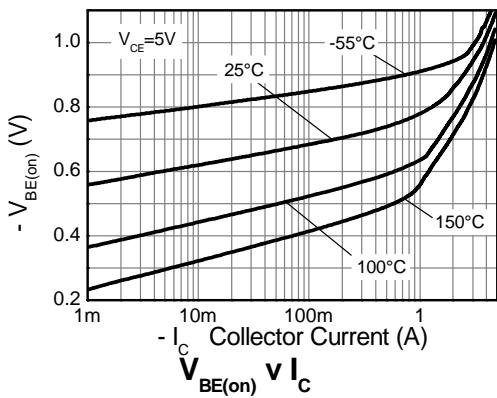
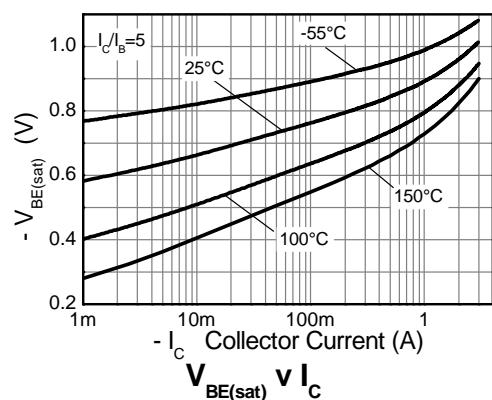
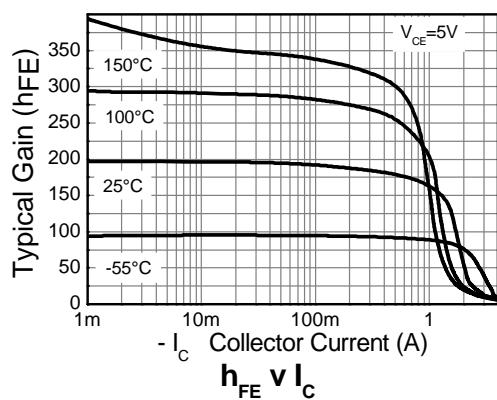
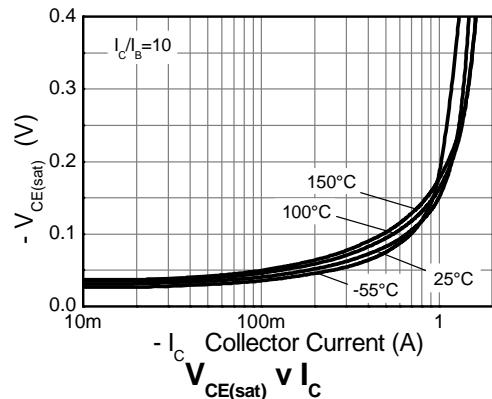
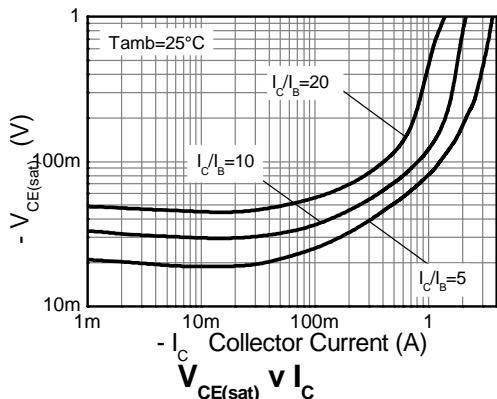
Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-Base Breakdown Voltage	BV_{CBO}	-220	-245		V	$I_C = -100\mu A$
Collector-Emitter Breakdown Voltage	BV_{CER}	-220	-245		V	$I_C = -1\mu A, R_{BE} \leq 1k\Omega$
Collector-Emitter Breakdown voltage	BV_{CEO}	-200	-225		V	$I_C = -10mA$ (*)
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	-8.4		V	$I_E = -100\mu A$
Collector-Base Cut-off Current	I_{CBO}		<1	-50 -0.5	nA μA	$V_{CB} = -200V$ $V_{CB} = -200V, T_{amb} = 100^\circ C$
Emitter Cut-off Current	I_{EBO}		<1	-10	nA	$V_{EB} = -6V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-37 -130 -135 -180	-50 -155 -160 -275	mV mV mV mV	$I_C = -0.1A, I_B = -10mA$ (*) $I_C = -0.5A, I_B = -25mA$ (*) $I_C = -1A, I_B = -100mA$ (*) $I_C = -2A, I_B = -400mA$ (*)
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-955	-1100	mV	$I_C = -2A, I_B = -400mA$ (*)
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-860	-1000	mV	$I_C = -2A, V_{CE} = -5V$ (*)
Static Forward Current Transfer Ratio	h_{FE}	100 100 20	195 170 50 5	300		$I_C = -10mA, V_{CE} = -5V$ (*) $I_C = -1A, V_{CE} = -5V$ (*) $I_C = -2A, V_{CE} = -5V$ (*) $I_C = -5A, V_{CE} = -5V$ (*)
Transition Frequency	f_T		105		MHz	$I_C = -100mA, V_{CE} = -10V$ $f = 50MHz$
Output Capacitance	C_{obo}		31		pF	$V_{CB} = -10V, f = 1MHz$ (*)
Delay Time	t_d		21		ns	$I_C = -1A, V_{CC} = -50V$, $I_{B1} = -I_{B2} = -100mA$
Rise Time	t_r		18		ns	
Storage Time	t_s		680		ns	
Fall Time	t_f		75		ns	

NOTES:

(*) Measured under pulsed conditions. Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

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Typical Characteristics

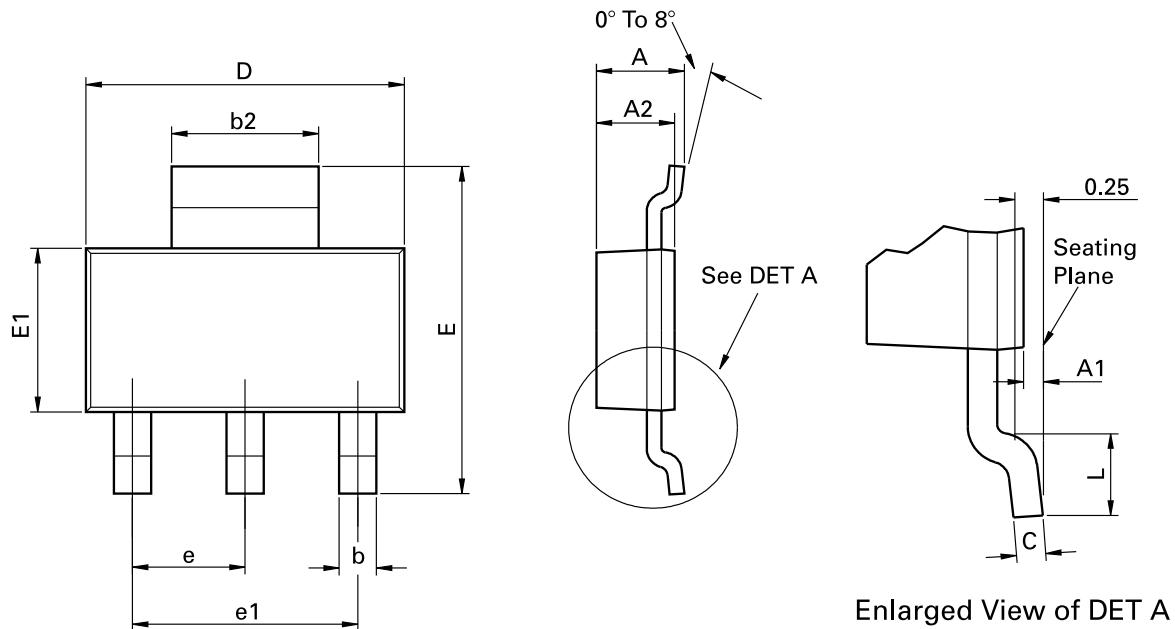


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Package Information – SOT223



Conforms to JEDEC TO-261 AA Issue B

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	-	1.80	-	0.071	e	2.30	BSC	0.0905	BSC
A1	0.02	0.10	0.0008	0.004	e1	4.60	BSC	0.181	BSC
b	0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
b2	2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
C	0.23	0.33	0.009	0.013	L	0.90	-	0.355	-
D	6.30	6.70	0.248	0.264	-	-	-	-	-

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- or
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"Active"	Product status recommended for new designs
"Last time buy (LTB)"	Device will be discontinued and last time buy period and delivery is in effect
"Not recommended for new designs"	Device is still in production to support existing designs and production
"Obsolete"	Production has been discontinued

Datasheet status key:

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"Issue"	This term denotes an issued datasheet containing finalized specifications. However, changes to specifications may occur, at any time and without notice.

Diodes sales offices

Sales offices

The Americas	Europe	Taiwan	Shanghai	Shenzhen	Korea
3050 E. Hillcrest Drive Westlake Village, CA 91362-3154 Tel: (+1) 805 446 4800 Fax: (+1) 805 446 4850	Kustermannpark Balanstraße 59, D-81541 München Germany Tel: (+49) 894 549 4900 Fax: (+49) 894 549 4949	7F, No. 50, Min Chuan Road Hsin-Tien Taipei, Taiwan Tel: (+886) 289 146 000 Fax: (+886) 289 146 639	Rm. 606, No.1158 Changning Road Shanghai, China Tel: (+86) 215 241 4882 Fax (+86) 215 241 4891	Room A1103-04, ANLIAN Plaza, #4018 Jintian Road Futian CBD, Shenzhen, China Tel: (+86) 755 882 849 88 Fax: (+86) 755 882 849 99	6 Floor, Changhwa B/D, 1005-5 Yeongtong-dong, Yeongtong-gu, Suwon-si, Gyeonggi-do, Korea 443-813 Tel: (+82) 312 731 884 Fax: (+82) 312 731 885